

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD

PART NUMBER: 1SR156-400

MANUFACTURER: ROHM

REMARK: TC=80C

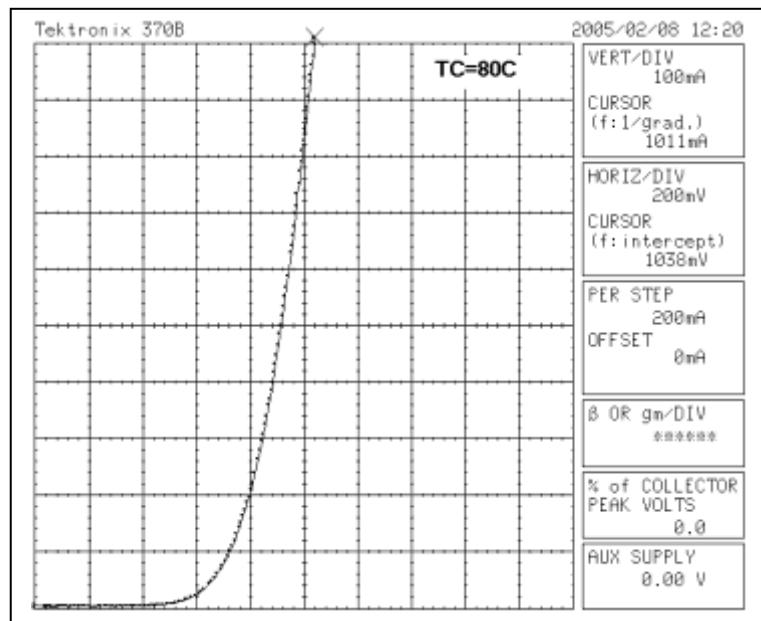


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

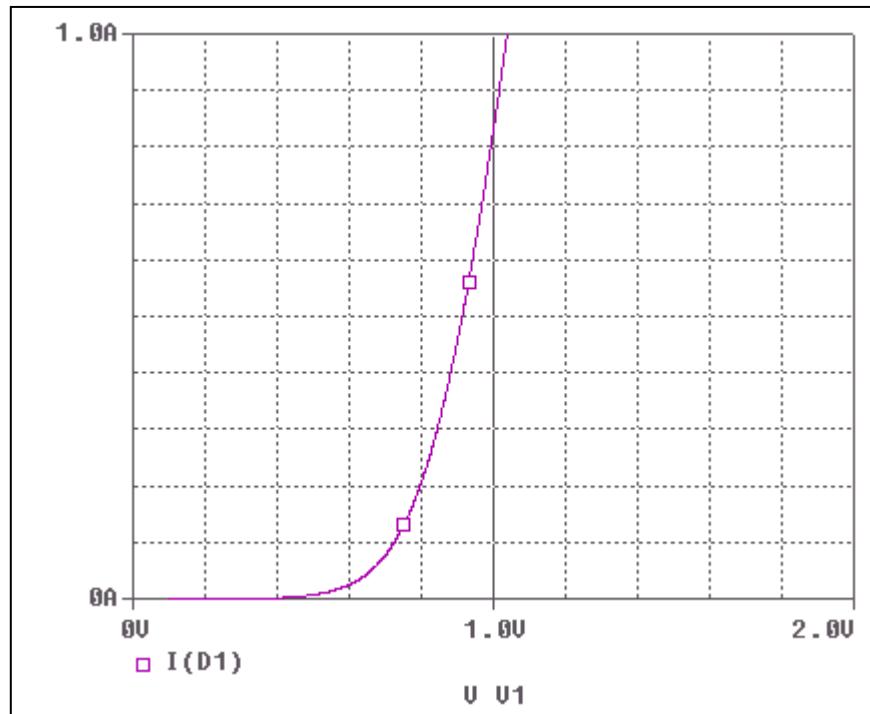
Forward Current Characteristic

Reference

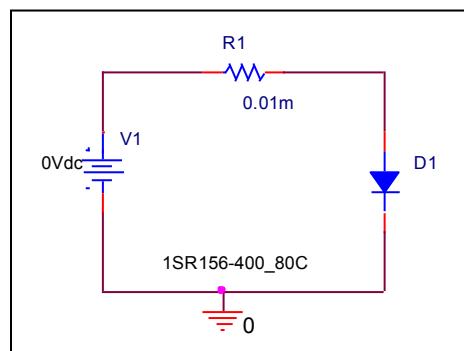


Forward Current Characteristic

Circuit Simulation Result

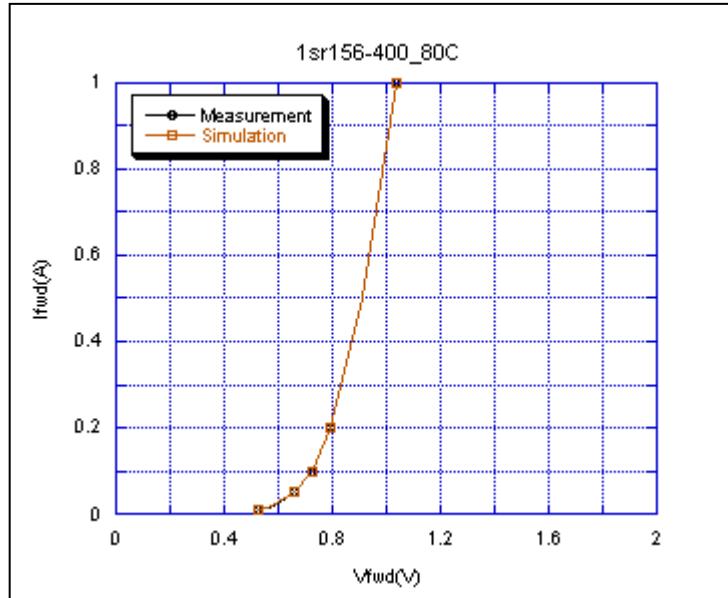


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

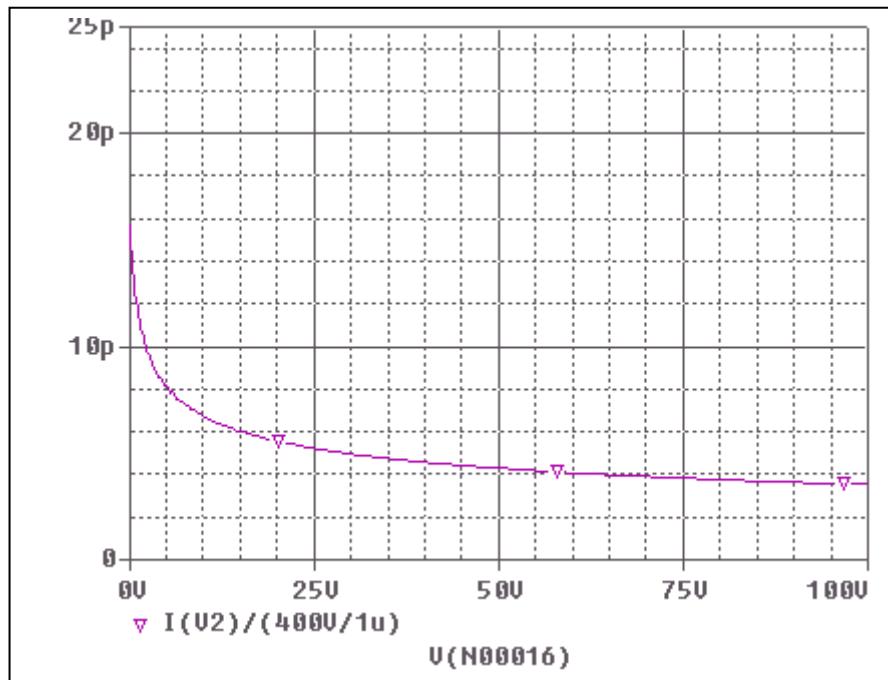


Simulation Result

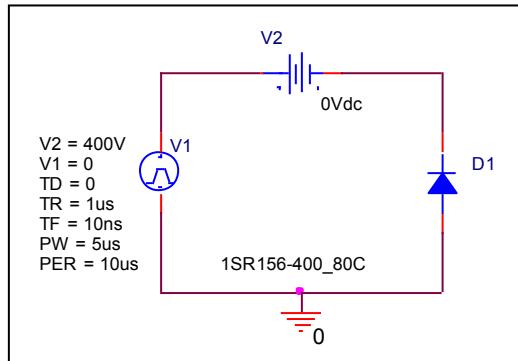
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.01	0.526	0.525	0.19
0.02	0.582	0.580	0.34
0.05	0.658	0.660	-0.30
0.1	0.726	0.724	0.28
0.2	0.796	0.796	0.00
0.5	0.914	0.913	0.11
1	1.038	1.038	0.00

Capacitance Characteristic

Circuit Simulation Result

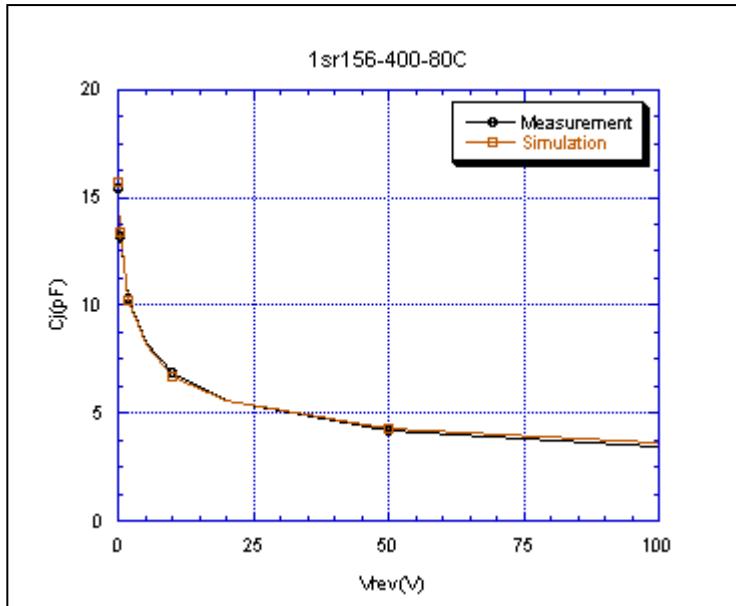


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

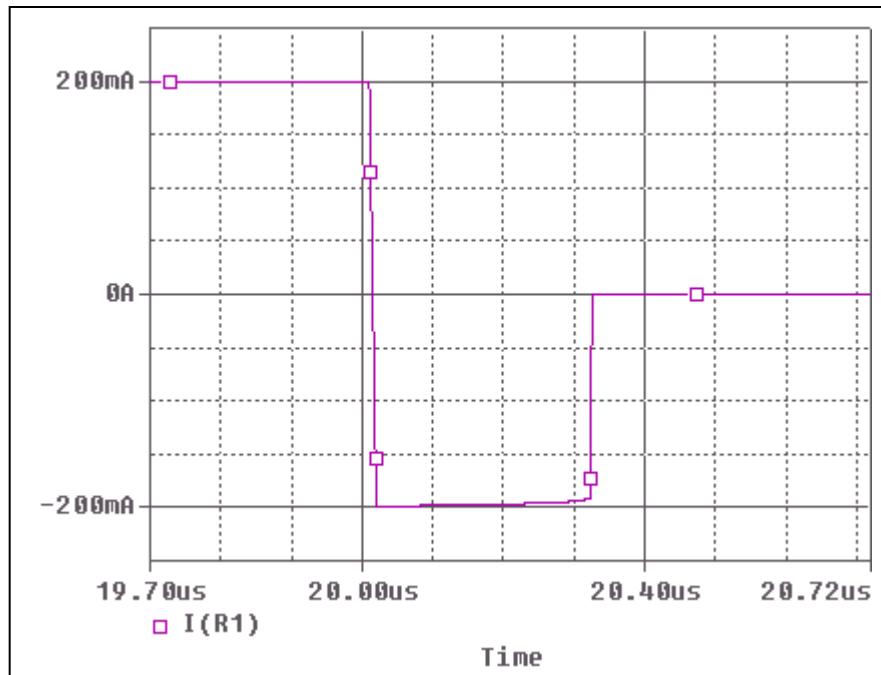


Simulation Result

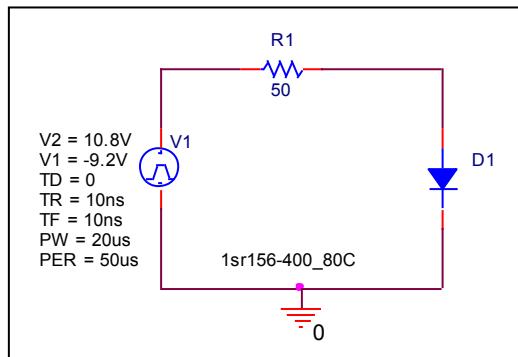
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	16.690	16.690	0.00
0.1	15.428	15.712	-1.84
0.2	14.699	14.828	-0.88
0.5	13.184	13.375	-1.45
1	11.852	11.904	-0.44
2	10.333	10.246	0.84
5	8.314	8.180	1.61
10	6.853	6.739	1.66
20	5.553	5.563	-0.18
50	4.153	4.294	-3.40
100	3.389	3.500	-3.28

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

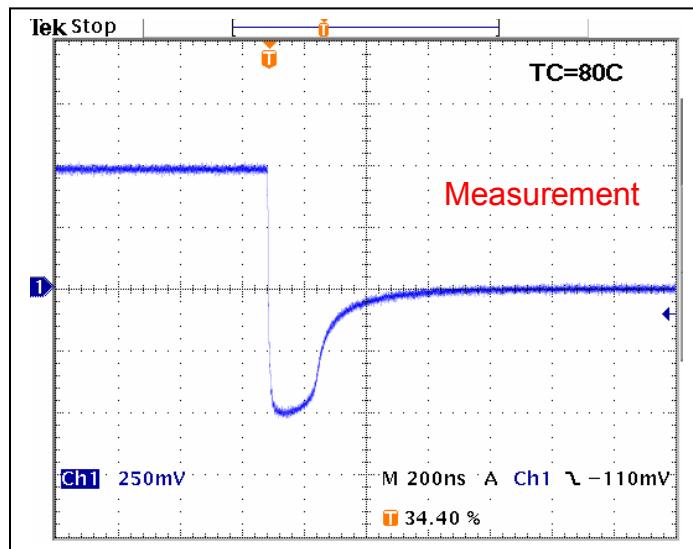


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	312.0	ns	310.0	ns	0.64

Reverse Recovery Characteristic

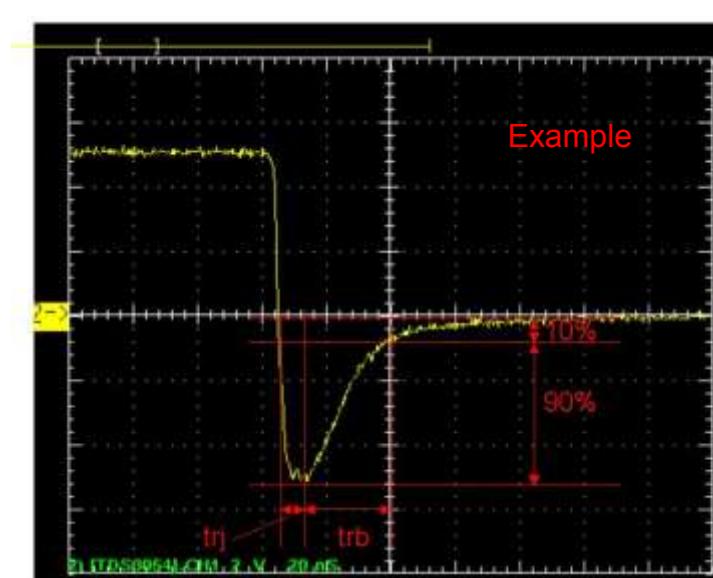
Reference



Trj = 56(ns)

Trb=256(ns)

Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb